



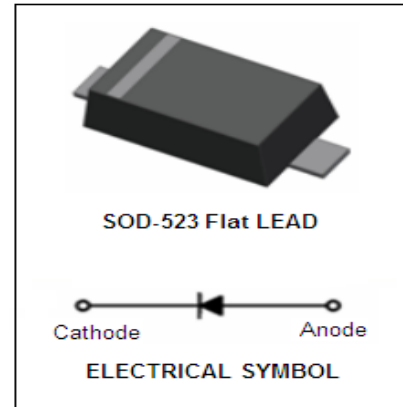
SLS SEMICONDUCTOR (SHENZHEN) CO.,LTD.

**SOD-523 封装二极管/SOD-523 Plastic-Encapsulate Diodes**

**BZX584C2V4~BZX584C39 (ZENER DIODES)**

**Features:**

- ◆ Planar die construction;
- ◆ 150mW power dissipation;
- ◆ Zener Voltage from 2.4V~39V;
- ◆ Ultra-Small Surface Mount



**Maximum ratings (Ta=25°C unless otherwise specified)**

Characteristic	Symbol	Value	Unit
Forward Voltage (Note 2) @I <sub>F</sub> =10mA	V <sub>RM</sub>	0.9	V
Power Dissipation (Note 1)	P <sub>D</sub>	0.15	W
Thermal Resistance Junction to Ambient Air	R <sub>θJA</sub>	833	°C/W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-65~150	°C



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**SOD-523 封装二极管/SOD-523 Plastic-Encapsulate Diodes**

Electrical characteristics (Ta=25°C unless otherwise specified)

TYPE	Marking	Zener Voltage range(note2)				Maximum Zener Impedance(Note 3)			Maximum Reverse Current (Note2)		Typical Temperature Coefficient @I <sub>ZT</sub> mV/°C	
		V <sub>Z</sub> @I <sub>ZT</sub>			I <sub>ZT</sub>	V <sub>Z</sub> @I <sub>ZT</sub>	V <sub>ZK</sub> @I <sub>ZK</sub>	I <sub>ZK</sub>	I <sub>R</sub>	V <sub>R</sub>	Min	Max
		Nom(V)	Min(V)	Max(V)	(mA)	Ω		(mA)	μA	V		
BZX584C2V4	Z11	2.4	2.2	2.6	5	100	600	1.0	50	1.0	-3.5	0
BZX584C2V7	Z12	2.7	2.5	2.9	5	100	600	1.0	20	1.0	-3.5	0
BZX584C3V0	Z13	3.0	2.8	3.2	5	95	600	1.0	10	1.0	-3.5	0
BZX584C3V3	Z14	3.3	3.1	3.5	5	95	600	1.0	5	1.0	-3.5	0
BZX584C3V6	Z15	3.6	3.4	3.8	5	90	600	1.0	5	1.0	-3.5	0
BZX584C3V9	Z16	3.9	3.7	4.1	5	90	600	1.0	3	1.0	-3.5	0
BZX584C4V3	Z17	4.3	4.0	4.6	5	90	600	1.0	3	1.0	-3.5	0
BZX584C4V7	Z1	4.7	4.4	5.0	5	80	500	1.0	3	2.0	-3.5	0.2
BZX584C5V1	Z2	5.1	4.8	5.40	5	60	480	1.0	2	2.0	-2.7	1.2
BZX584C5V6	Z3	5.6	5.2	6.0	5	40	400	1.0	1	2.0	-2.0	2.5
BZX584C6V2	Z4	6.2	5.8	6.6	5	10	150	1.0	3	4.0	0.4	3.7
BZX584C6V8	Z5	6.8	6.4	7.2	5	15	80	1.0	2	4.0	1.2	4.5
BZX584C7V5	Z6	7.5	7.0	7.9	5	15	80	1.0	1	5.0	2.5	5.3
BZX584C8V2	Z7	8.2	7.7	8.7	5	15	80	1.0	0.7	5.0	3.2	6.2
BZX584C9V1	Z8	9.1	8.5	9.6	5	15	100	1.0	0.5	6.0	3.8	7.0
BZX584C10	Z9	10	9.4	10.6	5	20	150	1.0	0.2	7.0	4.5	8.0
BZX584C11	Y1	11	10.4	11.6	5	20	150	1.0	0.1	8.0	5.4	9.0
BZX584C12	Y2	12	11.4	12.7	5	25	150	1.0	0.1	8.0	6.0	10.0
BZX584C13	Y3	13	12.4	14.1	5	30	170	1.0	0.1	8.0	7.0	11.0
BZX584C15	Y4	15	13.8	15.60	5	30	200	1.0	0.1	10.5	9.2	13.0
BZX584C16	Y5	16	15.3	17.1	5	40	200	1.0	0.1	11.2	10.4	14.0
BZX584C18	Y6	18	16.8	19.1	5	45	225	1.0	0.1	12.6	12.4	16.0
BZX584C20	Y7	20	18.8	21.2	5	55	225	1.0	0.1	14.0	14.4	18.0
BZX584C22	Y8	22	20.8	23.3	5	55	250	1.0	0.1	15.4	16.4	20.0
BZX584C24	Y9	24	22.8	25.6	5	70	250	1.0	0.1	16.8	18.4	22.0
BZX584C27	Y10	27	25.1	28.9	2	80	300	0.5	0.1	18.9	21.4	25.3
BZX584C30	Y11	30	28.00	32.0	2	80	300	0.5	0.1	21.0	24.4	29.4
BZX584C33	Y12	33	31.0	35.0	2	80	325	0.5	0.1	23.1	27.4	33.4
BZX584C36	Y13	36	34.0	38.0	2	90	350	0.5	0.1	25.2	30.4	37.4
BZX584C39	Y14	39	37.0	41.0	2	130	350	0.5	0.1	27.3	33.4	41.2

Note:

1. Valid provided that device terminals are kept at ambient temperature;
2. Tested with pulses, period=5ms, pulse width=300 μS;
3. f=1kHz;